## LISTING OF THE CLAIMS

This listing of claims will replace all prior versions, and listings of claims in the application:

## **Listing of Claims:**

1-42. (Canceled)

- 43. (Previously introduced) In a process for manufacturing a semiconductor device that has performance characteristics that may vary during the initial period of operation, a method for stabilizing the device comprising:
  - a. applying a test current to the semiconductor device for a brief period of time; and
  - b. repeating step (a) above at an incremental current over the test current until the test current is above the normal operating current of the semiconductor device.
- 44. (Previously introduced) The method of claim 43, further comprising providing an elevated ambient temperature for the semiconductor device during the steps of providing a sequence of test currents.
- 45. (Previously introduced) The method of claim 44, wherein the dwell time of each application of a test current is about 15 ms.
- 46. (Previously introduced) The method of claim 43, wherein the number of cycles of providing a test current is about four.
- 47. (Previously introduced) The method of claim 43, wherein the semiconductor device is a vertical cavity surface emitting laser and the step

PALOALTO 49684 (2K) -2-

Appl. No. 10/670,163 Amdt. dated Feb. 1, 2005 Reply to Office action of Jan. 11, 2005

of providing a test current to said semiconductor device further includes sequentially providing a sequence of test currents, to each of the vertical cavity surface emitting lasers on a wafer under test.

48. (Previously introduced) The method of claim 43, wherein the scan current ramp rate, the number of scans per device, the dwell time, the peak value of input current, and the ambient temperature are adjusted for each process.

PALOALTO 49684 (2K) -3-